

APPLICATION FOR UNITED STATES PATENT DECLARATION AND POWER OF ATTORNEY

As a below named inventor, I declare that my residence, post office address and citizenship are as stated below next to my name; that I verily believe that I am the original, first and sole inventor if only one name is listed below, or an original, first and joint inventor is plural inventors are named below, of the subject matter which is claimed and for which a patent is sought on the invention entitled as set forth below, which is described in the attached specification; that I have reviewed and understand the contents of the specification, including the claims, as amended by any amendment specifically referred to in the oath or declaration; that no application for patent or inventor's certificate on this invention has been filed by me or my legal representatives or assigns in any country foreign to the United States of America; and that I acknowledge my duty to disclose information which is material to the patentability of this application in accordance with Title 37, Code of Federal Regulations, section 1.56;

I further declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true, and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under section 1001 of Title 18 of the United States Code, and that such willful false statements may jeopardize the validity of the application or any patent issuing thereon.

TITLE OF INVENTION:		
METHODS FOR FABRICATING LOW	CHC DEGRADATION MOSFET	
1	PPOINT THE FOLLOWING ATTORNEYS TO PROS ID TRADEMARK OFFICE CONNECTED THEREWIT	
Practitioners at	Customer Number: 23494	
	hweiler, Reg. No. 36,981 an, Reg. No. 43,672	
SEND CORRESPONDENCE TO:		DIRECT TELEPHONE CALLS TO:
Jacqueline J. Garner Texas Instruments Incorporated PO Box 655474, MS 3999 Dallas, TX 75265		Jacqueline J. Garner (972) 271-1176
NAME OF INVENTOR: (1)	NAME OF INVENTOR: (2)	NAME OF INVENTOR: (3)
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Country of Citizenship: United States	Country of Citizenship:	Country of Citizenship:
Signature of Inventor:	Signature of Inventor:	Signature Of Inventor:
Signature of Inventor: To zet (, lu 70)		
Date:	Date:	Date:
12/5/2001		

Attorney Docket No.: TI-32931

ITLE OF INVENTION [.] METHODS FOR FABRICATING LOW C	HC DEGRADATION MOSFET	FOUTE THIS APPLICATION AND
POWER OF ATTORNEY: I HEREBY APP PRANSACT ALL BUSINESS IN THE PATENT AND Practitioners at C	POINT THE FOLLOWING ATTORNEYS TO PROSE TRADEMARK OFFICE CONNECTED THEREWIT Customer Number: 23494	H.
SEND CORRESPONDENCE TO: Jacqueline J. Garner Tayas Instruments Incorporated	n, Reg. No. 43,872	DIRECT TELEPHONE CALLS TO: Jacqueline J. Garner (972) 271-1176
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Country of Citizenship: Great Britain Signature of Inventor: Lodd Date:	Country of Citizenship: United States Signature of Inventor: Date: \alpha/b/c/	Country of Citizenship: Japan Signature Of Inventor: Date: 12/6/0/